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**آترین الکترونیک**

تخصص، تنوع و کیفیت

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تهران پاساژ امجد طبقه 1 واحد 16



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### General Description

This IGBT is produced using advanced MagnaChip's Field Stop Trench IGBT Technology, which provides high switching series and excellent quality.

This device is for PFC, UPS & Inverter applications.

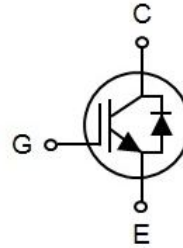
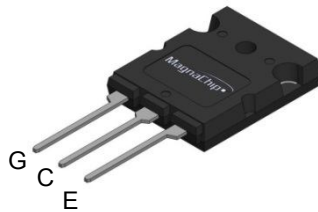
### Features

- High Speed Switching & Low Power Loss
- $V_{CE(sat)} = 1.95V @ I_C = 40A$
- $E_{off} = 0.35mJ @ T_C = 25^\circ C$
- High Input Impedance
- $t_{rr} = 80ns (typ.) @ di_F/dt = 1000A/\mu s$
- Maximum junction temperature  $175^\circ C$

### Applications

- PFC
- Welder
- UPS
- IH Cooker
- PV Inverter

TO-247



### Maximum Rating

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	$V_{CE}$	650	V
DC collector current, limited by $T_{vjmax}$	$I_C$	$T_C=25^\circ C$	80
		$T_C=100^\circ C$	40
Pulsed collector current, $t_p$ limited by $T_{vjmax}$	$I_{Cpuls}$	160	A
Turn off safe operating area $V_{CE} \leq 600V, T_{vj} \leq 175^\circ C$	-	160	A
Diode forward current limited by $T_{vjmax}$	$I_F$	$T_C=25^\circ C$	40
		$T_C=100^\circ C$	20
Diode pulsed current, $t_p$ limited by $T_{vjmax}$	$I_{Fpuls}$	160	A
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Power dissipation	$P_D$	$T_C=25^\circ C$	375
		$T_C=100^\circ C$	188
Short circuit withstand time $V_{CC} \leq 400V, V_{GE} = 15V, T_{vj} = 150^\circ C$ Allowed number of short circuits < 1000 Time between short circuits $\geq 1.0s$	tsc	5	$\mu s$
Operating Junction temperature range	$T_{vj}$	-40~175	$^\circ C$
Storage temperature range	$T_{stg}$	-55~150	$^\circ C$
Soldering temperature Wave soldering 1.6 mm (0.063 in.) from case for 10s		260	$^\circ C$
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

### Thermal Characteristic

Parameter	Symbol	Rating	Unit
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	$^\circ C/W$
Thermal resistance junction-to-case for IGBT	$R_{\theta JC}$	0.4	
Thermal resistance junction-to-case for Diode	$R_{\theta JC}$	1.2	

### Ordering Information

Part Number	Marking	Temp. Range	Package	Packing	RoHS Status
MBQ40T65FDSC	40T65FDSC	-55~175°C	TO-247	Tube	Halogen Free

### Electrical Characteristic (T<sub>vj</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
<b>Static Characteristic</b>							
Collector-emitter breakdown voltage	BV <sub>CES</sub>	I <sub>C</sub> = 2mA, V <sub>GE</sub> = 0V	650	-	-	V	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V, T <sub>vj</sub> = 25°C		1.95	2.4	V	
		I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V, T <sub>vj</sub> = 175°C		2.3			
Diode forward voltage	V <sub>F</sub>	V <sub>GE</sub> = 0V, I <sub>F</sub> = 20A	T <sub>vj</sub> = 25°C		1.3	1.9	V
			T <sub>vj</sub> = 125°C		1.15		
			T <sub>vj</sub> = 175°C		1.1		
Gate-emitter threshold voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 0.58mA	4.0	5.0	6.0	V	
Zero gate voltage collector current	I <sub>CES</sub>	V <sub>CE</sub> = 650V, V <sub>GE</sub> = 0V	T <sub>vj</sub> = 25°C	-	-	40	μA
			T <sub>vj</sub> = 175°C	-	-	1000	
Gate-emitter leakage current	I <sub>GES</sub>	V <sub>GE</sub> = 20V, V <sub>CE</sub> = 0V	-	-	±100	nA	
Transconductance	g <sub>fs</sub>	V <sub>CE</sub> = 20V, I <sub>C</sub> = 40A,		17.0		S	

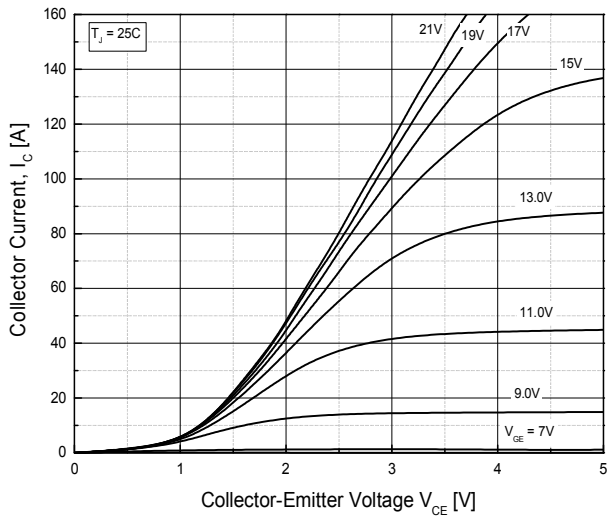
### Dynamic Characteristic

Total gate charge	Q <sub>g</sub>	V <sub>CE</sub> = 520V, I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V	-	219		nC
Gate-emitter charge	Q <sub>ge</sub>		-	26		
Gate-collector charge	Q <sub>gc</sub>		-	115		
Input capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 25V, V <sub>GE</sub> = 0V, f = 1MHz	-	2818	-	pF
Reverse transfer capacitance	C <sub>res</sub>		-	131	-	
Output capacitance	C <sub>oes</sub>		-	209	-	
Internal emitter inductance measured 5mm (0.197 in.) from case	L <sub>E</sub>		-	13.0	-	nH
Short circuit collector current Max. 1000 short circuits Time between short circuits: ≥ 1.0s	I <sub>C(SC)</sub>	V <sub>GE</sub> = 15V, V <sub>CC</sub> = 400V, t <sub>SC</sub> ≤ 5μs, T <sub>vj</sub> = 150°C	-	180	-	A

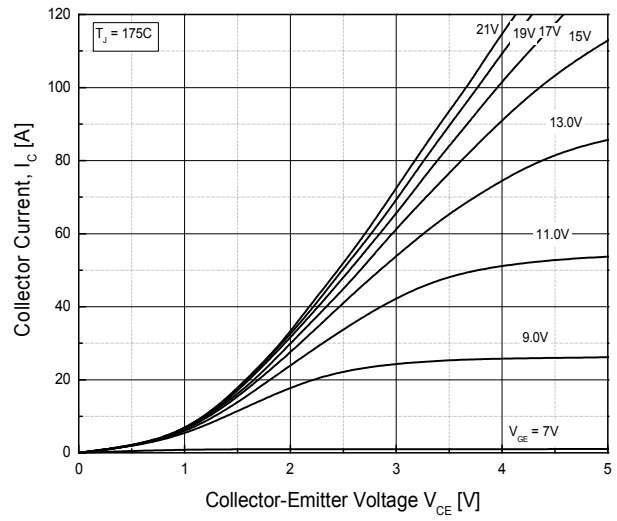
### Switching Characteristic

Turn-on delay time	t <sub>d(on)</sub>	V <sub>GE</sub> = 15V, V <sub>CC</sub> = 400V, I <sub>C</sub> = 40A, R <sub>G</sub> = 7.9Ω, Inductive Load, T <sub>vj</sub> = 25°C	-	58	-	ns
Rise time	t <sub>r</sub>		-	54	-	
Turn-off delay time	t <sub>d(off)</sub>		-	245	-	
Fall time	t <sub>f</sub>		-	40	-	mJ
Turn-on switching energy	E <sub>on</sub>		-	1.15	-	
Turn-off switching energy	E <sub>off</sub>		-	0.35	-	
Total switching energy	E <sub>ts</sub>		-	1.50	-	
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 20A, di <sub>F</sub> /dt = 1000A/μs, T <sub>vj</sub> = 25°C	-	80	-	ns
Reverse recovery current	I <sub>rr</sub>		-	25	-	A
Reverse recovery charge	Q <sub>rr</sub>		-	1.0	-	μC
Rate of fall of reverse recovery current during t <sub>b</sub>	di <sub>rr</sub> /dt		-	-950	-	A/μs

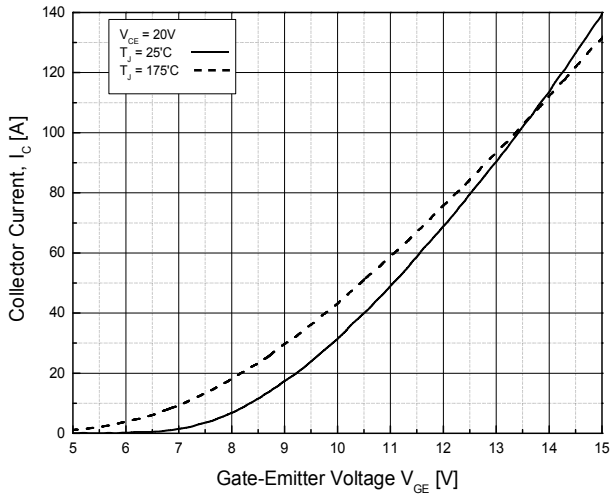
Switching Characteristic						
Turn-on delay time	$t_{d(on)}$	$V_{GE} = 15V, V_{CC} = 400V,$ $I_C = 40A, R_G = 7.9\Omega,$ Inductive Load, $T_{vj} = 175^\circ C$	-	61	-	ns
Rise time	$t_r$		-	60	-	
Turn-off delay time	$t_{d(off)}$		-	260	-	
Fall time	$t_f$		-	38	-	
Turn-on switching energy	$E_{on}$		-	1.80	-	mJ
Turn-off switching energy	$E_{off}$	-	0.38	-		
Total switching energy	$E_{ts}$	-	2.18	-		
Reverse recovery time	$t_{rr}$	$I_F = 20A, di_F/dt = 1000A/\mu s,$ $T_{vj} = 175^\circ C$	-	145	-	ns
Reverse recovery current	$I_{rr}$		-	44	-	A
Reverse recovery charge	$Q_{rr}$		-	3.2	-	nC
Rate of fall of reverse recovery current during $t_b$	$di_{rr}/dt$		-	-680	-	A/ $\mu s$



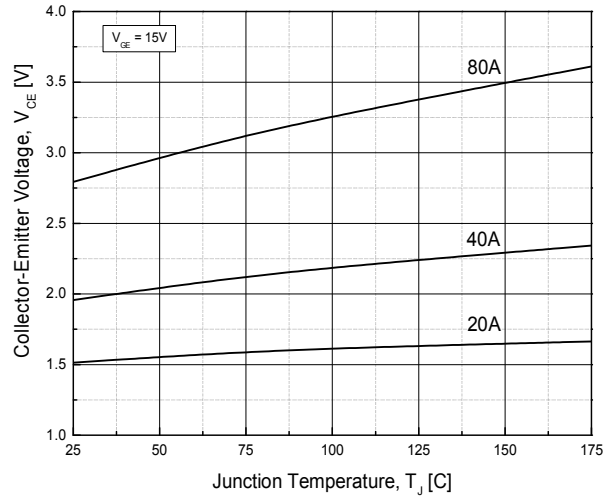
**Fig.1 Typical Output Characteristics ( $T_j = 25^\circ\text{C}$ )**



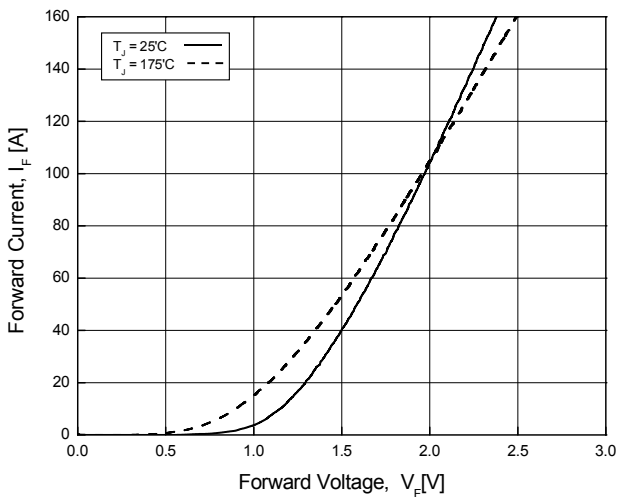
**Fig.2 Typical Output Characteristics ( $T_j = 175^\circ\text{C}$ )**



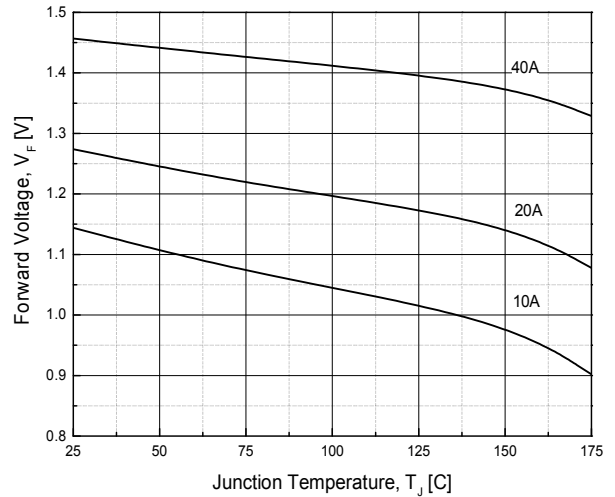
**Fig.3 Typical Transfer Characteristics**



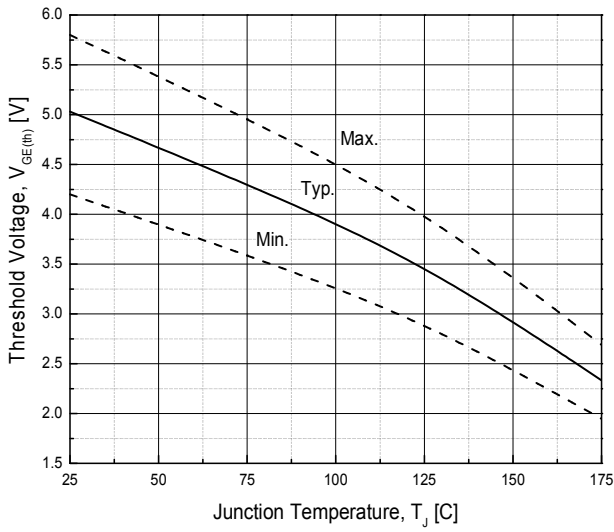
**Fig.4 Typical Collector-Emitter Saturation Voltage - Junction Temperature**



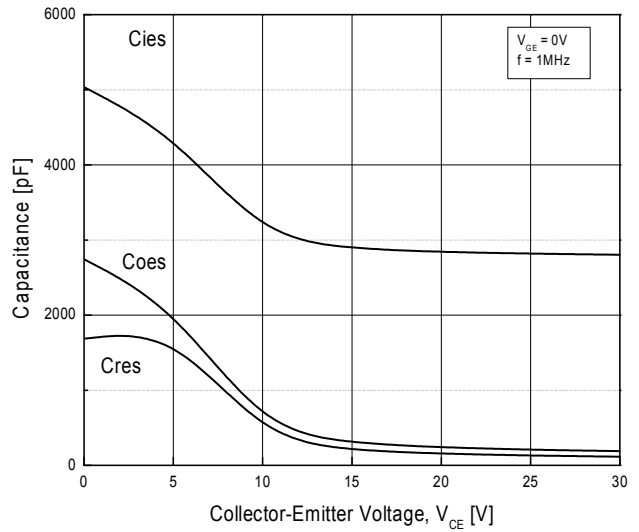
**Fig.5 Diode Forward Characteristics**



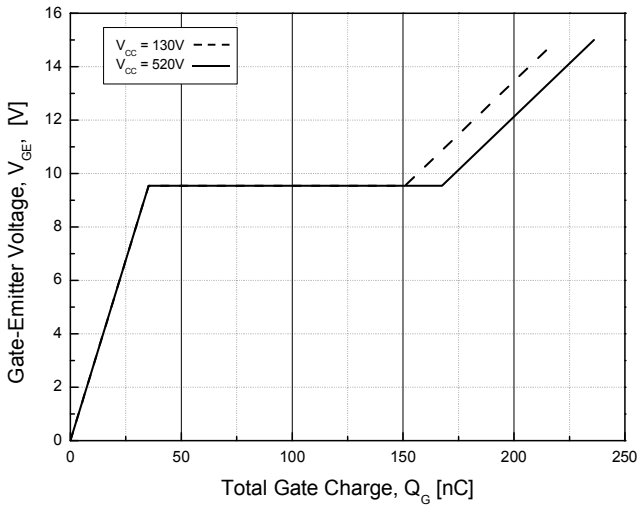
**Fig.6 Diode Forward-Junction Temperature**



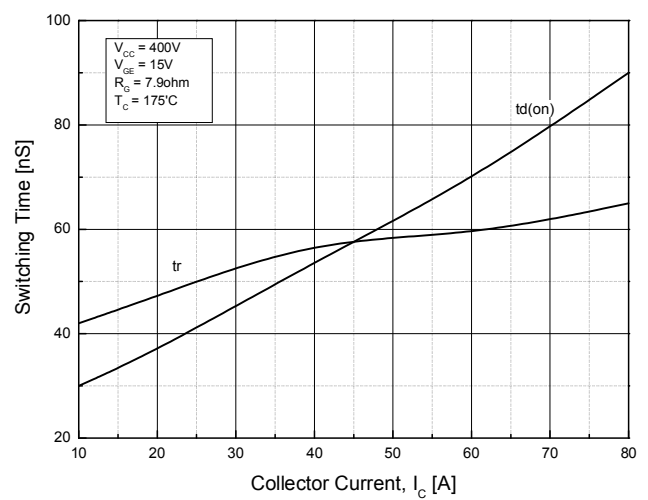
**Fig.7 Threshold Voltage-Junction Temperature**



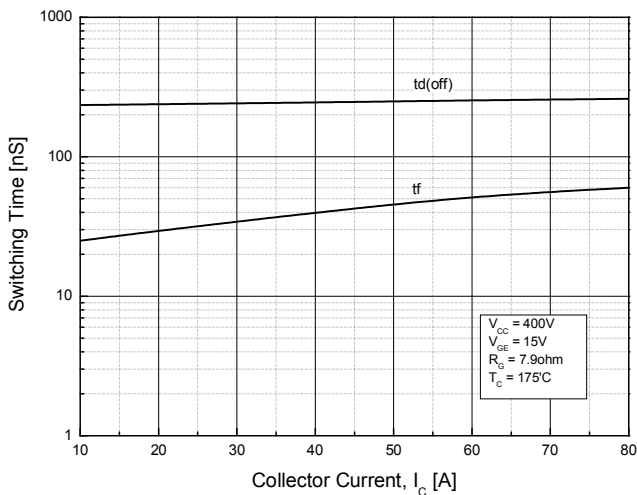
**Fig.8 Typical Capacitance**



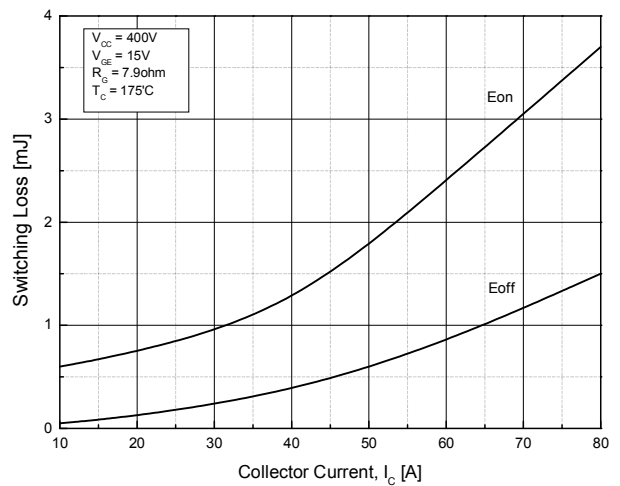
**Fig.9 Typical Gate Charge**



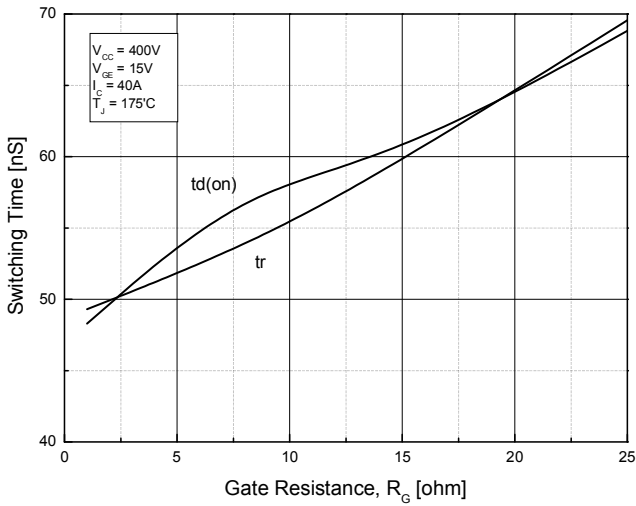
**Fig.10 Typical Turn on-Collector Current**



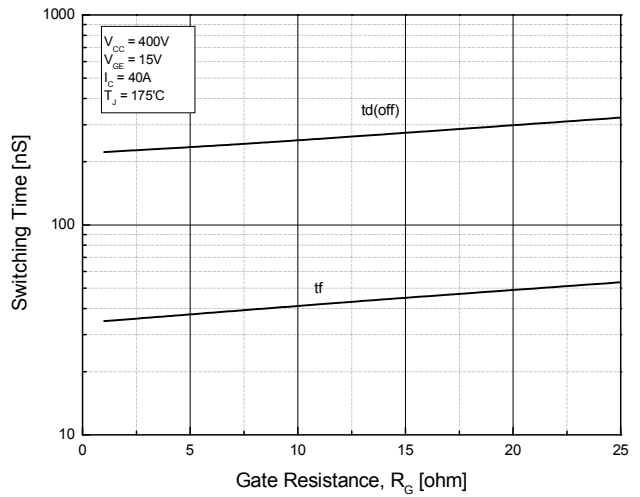
**Fig.11 Typical Turn off-Collector Current**



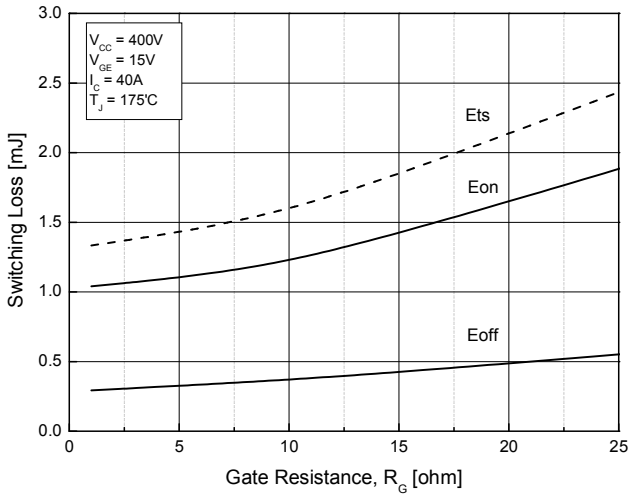
**Fig.12 Switching Loss-Collector Current**



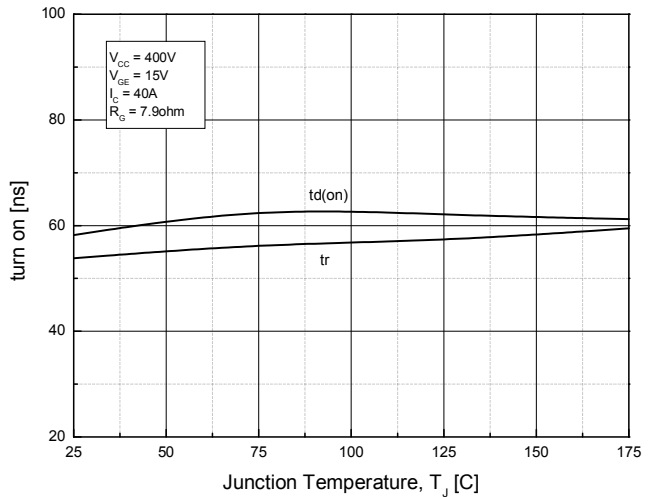
**Fig.13 Turn on Characteristics-Gate Resistance**



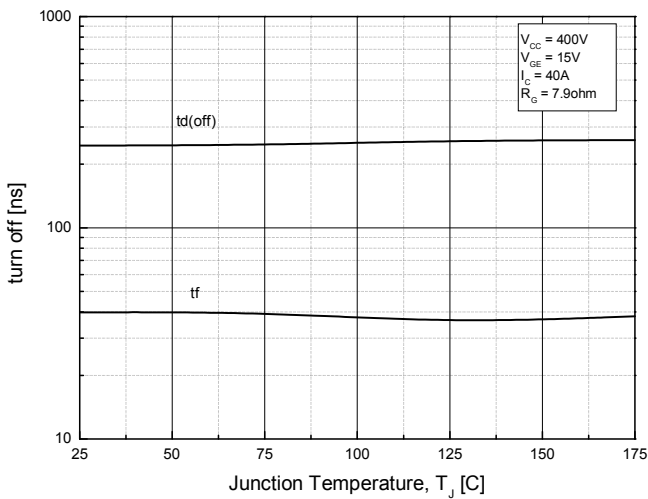
**Fig.14 Turn off Characteristics-Gate Resistance**



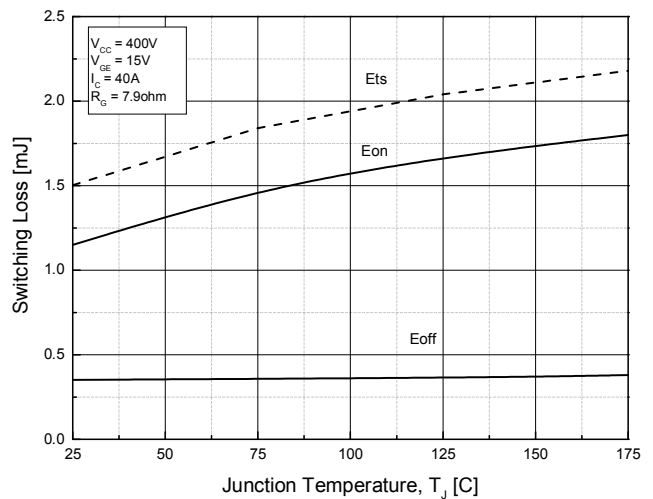
**Fig.15 Switching Loss-Gate Resistance**



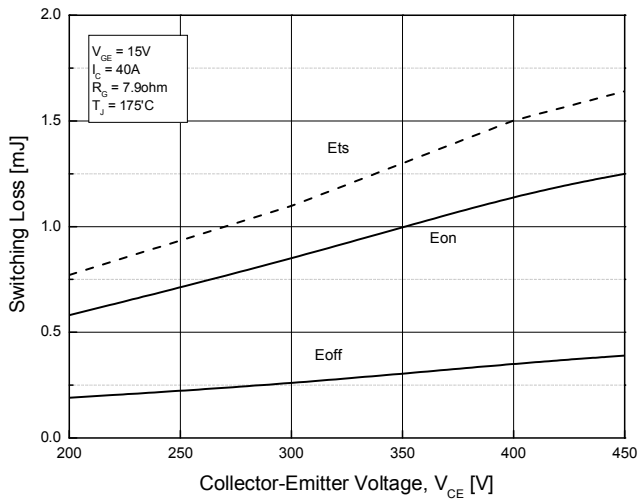
**Fig.16 Turn on Characteristics -Junction Temperature**



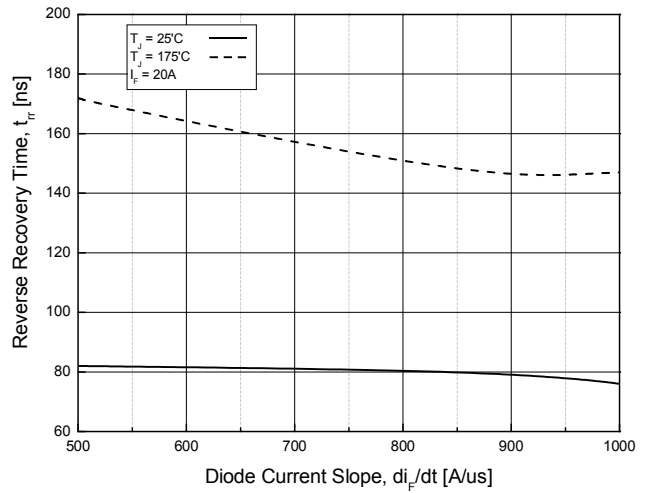
**Fig.17 Turn off Characteristics -Junction Temperature**



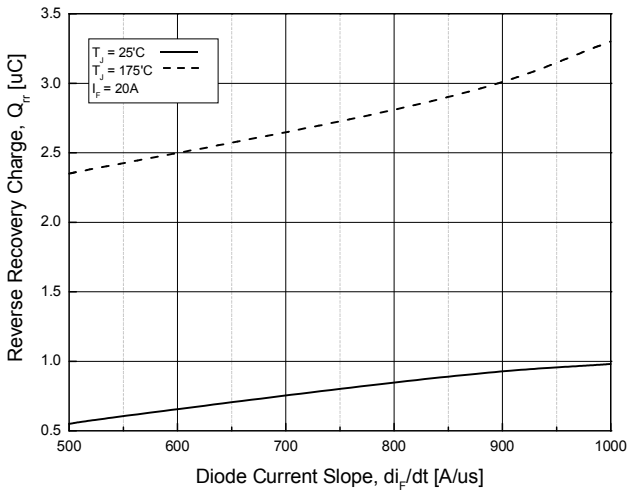
**Fig.18 Switching Loss-Junction Temperature**



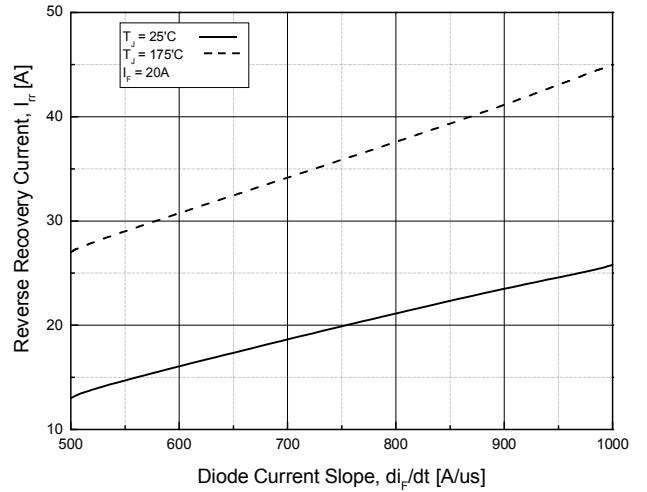
**Fig.19 Switching Loss-Collector Emitter Voltage**



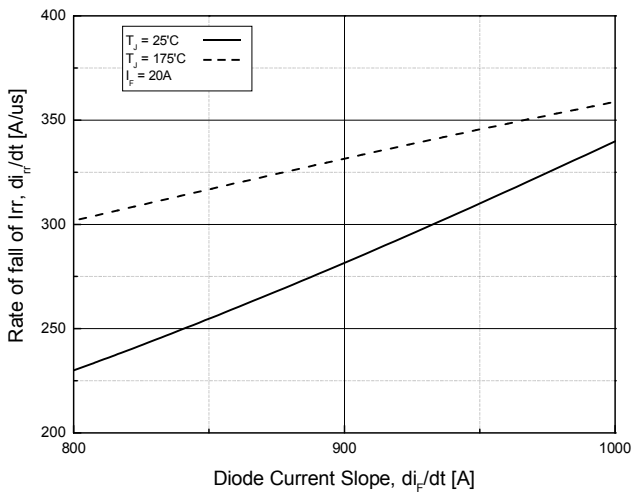
**Fig.20 Reverse Recovery Time -Diode current slope**



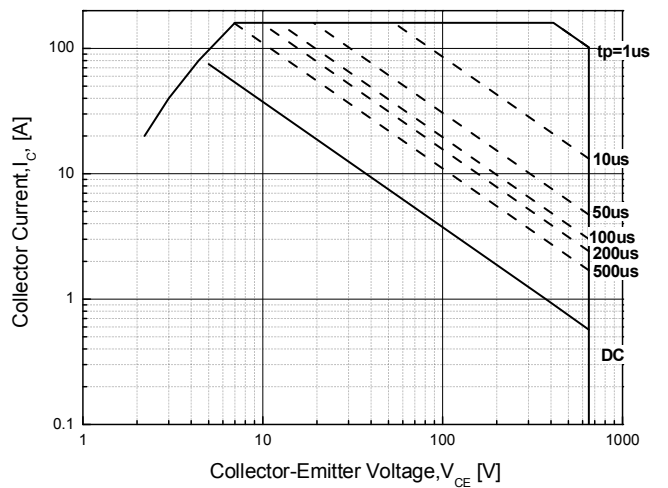
**Fig.21 Reverse Recovery Charge -Diode Current Slope**



**Fig.22 Reverse Recovery Current -Diode current slope**

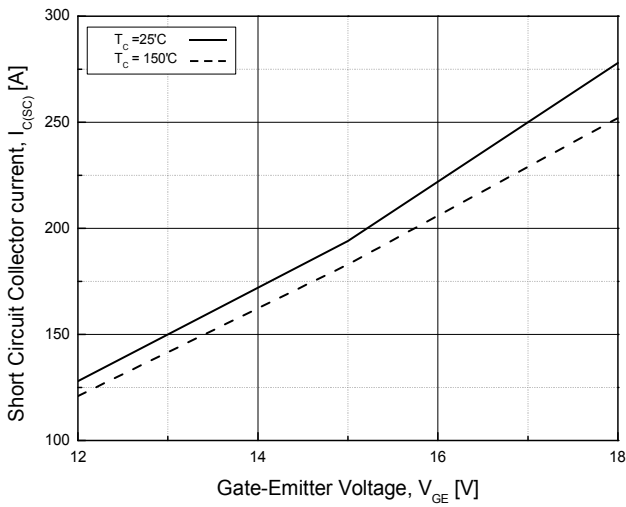


**Fig.23 Rate of fall of reverse recovery current -Diode Current Slope**

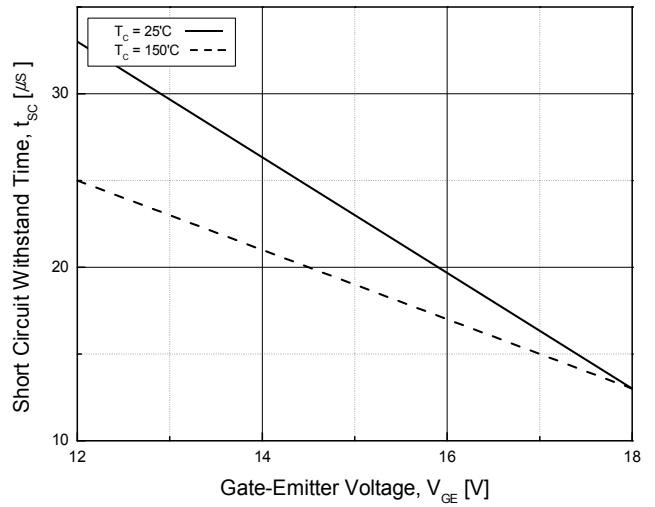


**Fig.24 Forward Bias Safe Operating Area**

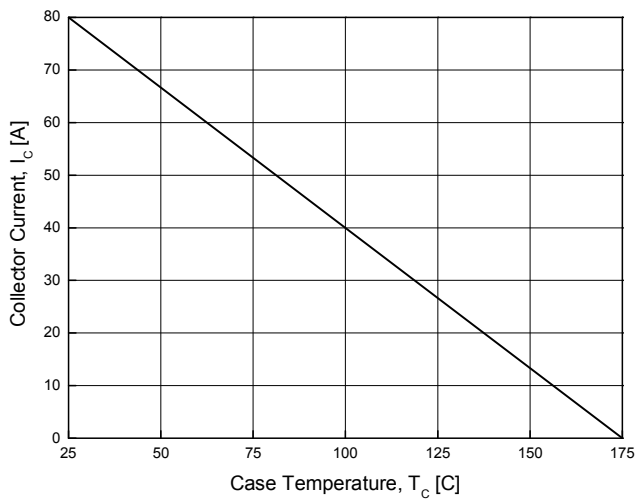




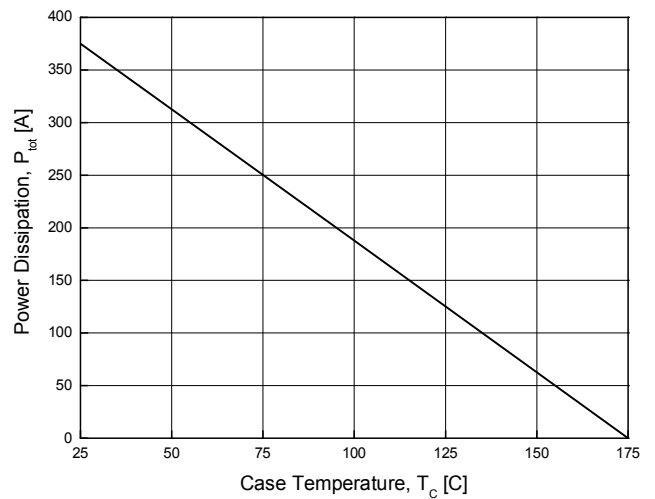
**Fig.25 Typical Short Circuit Collector Current**



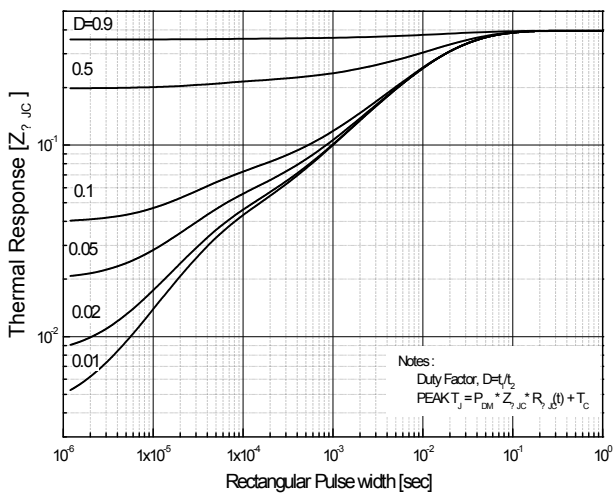
**Fig.26 Typical Short Circuit Withstand Time**



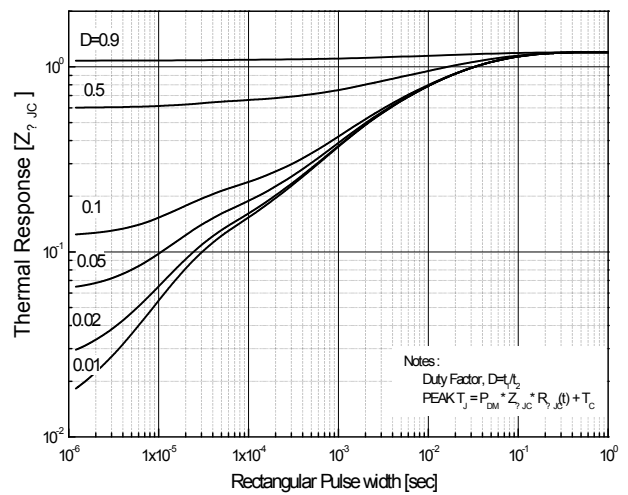
**Fig.27 Case Temperature-Collector Current**



**Fig.28 Power Dissipation-Case Temperature**



**Fig.29 IGBT Transient Thermal Impedance**

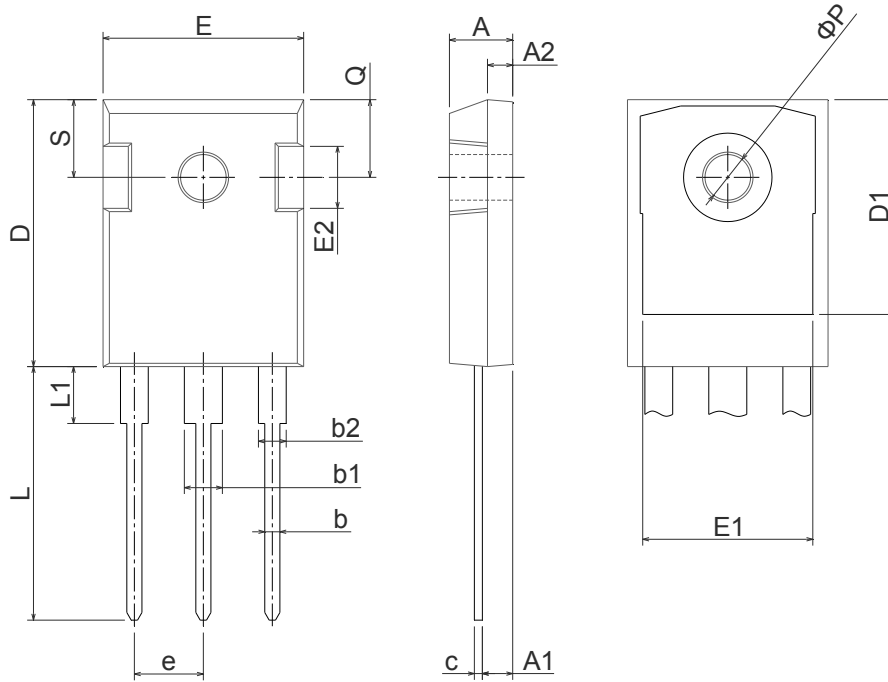


**Fig.30 FRD Transient Thermal Impedance**

**Physical Dimension**

**TO-247**

Dimensions are in millimeters, unless otherwise specified



Dimension	Min(mm)	Max(mm)
A	4.70	5.31
A1	2.20	2.60
A2	1.50	2.49
b	0.99	1.40
b1	2.59	3.43
b2	1.65	2.39
c	0.38	0.89
D	20.30	21.46
D1	13.08	-
E	15.45	16.26
E1	13.06	14.02
E2	4.32	5.49
e	5.45BSC	
L	19.81	20.57
L1	-	4.50
ΦP	3.50	3.70
Q	5.38	6.20
S	6.15BSC	

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The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.

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